भारतीय सूचना प्रौद्योगिकी अभिकल्पना, 🛫 एवं विनिर्माण संस्थान, कांचीपुरम



INDIAN INSTITUTE OF INFORMATION TECHNOLOGY, DESIGN AND MANUFACTURING, KANCHEEPURAM

Non-Teaching Recruitment

Question Paper

Name of the Candidate	:	
Application No.	:	
Name of the Post		Technical Officer (ECE)
Exam Level	:	Screening Test (Level-1)
Date of Exam:	:	27.11.2023
Duration	118.0	150 Minutes
Total Marks		100

Instructions to the Candidates:

- 1. This Question paper contains printed pages with 100 questions.
- 2. All questions are multiple choice type questions (MCQs) with four choices (a), (b), (c), (d).
- 3. Candidates are not allowed to carry any paper, notes, books, gadgets etc. to the examination hall. Any candidate found using or in possession of such unauthorized materials or involved in copying or impersonation or adopting unfair means or behaviors will be disqualified and may be subjected to penal action.
- 4. There is only one correct answer. Choose the answer from among the four options given and mark the answer by darkening the appropriate bubble marked a, b, c, or d in the attached OMR.
- 5. Each question carries ONE (1) mark only. 1 mark will be awarded for each correct answer; 0.25 mark will be deducted for each wrong answers. (Please refer instructions given at the back side of OMR Sheet)

1.	coupled to each other the coefficient	ected in series and are also magnetically at of coupling being 0.1. The total	
	inductance of the combination can		
	(a) 0.4 H	(b) 3.2 H	
	(c) 4.0 H	(d) 4.4 H	
2.	The Nodal method of circuit analyst		
	(a) KVL and Ohm's law	(b) KCL and Ohm's law	
	(c) KCL and KVL	(d) KCL, KVL and Ohm's law	
3.		edges to form a cube. The resistance	
	between two diagonally opposite corners of the cube is		
	(a) $5/6 \Omega$	(b) 1 Ω	
	(c) 6/5 Ω	(d) $3/2 \Omega$	
4.		plex network connected to a load can be	
	replaced with an equivalent impedance		
	(a) in series with a current source		
	(b) in parallel with a voltage source		
	(c) in series with a voltage source		
	(d) in parallel with a current source		
5.		n internal impendence of $(4 + j3)\Omega$. If a	-
		this source has to extract the maximum	
	power out of the source, its value in		
	(a) 3	(b) 4	
	(c) 5	(d) 7	
6.	A load, $Z_L = R_L + jX_L$ is to be mate	hed using an ideal transformer, to a	
		$Z_s = R_s + jX_s$. The turn's ratio of the	
	transformer required is		
	(a) $\sqrt{ Z_L/Z_s }$	(b) $\sqrt{ R_L/R_S }$	
	$(c) \sqrt{ R_L/Z_s }$	$(d) \sqrt{Z_L/R_s}$	
7.	A DC voltage source is connected a	across a series R-L-C circuit, Under steady	
	state conditions, the applied DC vo		
	(a) R only	(b) L only	
	(c) C only	(d) R and L combination	
0	In a serie DIC : 'AD OLO I	111 1.C 1/400 P m	
8.		= 1H and C = $1/400\mu$ F. The resonant	
	frequency is	(1) 1/ 104 II	
	(a) $2 \times 10^4 \text{ Hz}$	(b) $1/\pi \times 10^4 \text{ Hz}$	
0	(c) 10 ⁴ Hz	(d) $2\pi \times 10^4 \text{ Hz}$	
9.		s impedance $\sqrt{3}$ Z, then each branch of the	
	equivalent Wye circuit has impedar		
	(a) $Z/\sqrt{3}$	(b) 3Z	
10	(c) $3\sqrt{3}Z$	(d) Z/3	_
10.	I.	o port network implies that the network is	
	a (a) maximum and matrix and	(1)1	
	(a) reciprocal network	(b) lumped element network	
1 1	(c) lossless network	(d) unilateral element network	
11.	II .	or a network with n nodes and b branches	
	is	(1) 1	
	(a) $n-1$	(b) b – n	
	(c) b - n + 1	(d) independent of the number of nodes	

12.	Superposition theorem is NOT applicable to networks containing (a) Nonlinear elements (b) Dependent current sources (c) Dependent current sources		
	(d) Transformers		
13.	Which of the following cannot be the fourier series expansion of a periodic		
10.	signal?		
14.			
17.	Choose the function $f(t)$; $-\infty < t < +\infty$, for which a fourier series cannot be defined		
	() 0 1 (0 5)		
	(a) $3 \sin (25t)$ (b) $4 \cos (20t + 3) + 2 \sin (10t)$		
1.5	$ (c) \exp(- t)\sin(25t) $ (d) 1		
15.	The Fourier series of an odd periodic function contains only		
	(a) odd harmonics (b) even harmonics		
	(c) cosine terms (d) sine terms		
16.	The trigonometric fourier series of an even function does not have the		
	(a) dc term (b) cosine term		
	(c) sine term (d) odd harmonic terms		
17.	The amplitude spectrum of a Gaussian pulse is		
	(a) uniform (b) a sine function		
	(c) Gaussian (d) an impulse function		
18.	If a signal f(t) has energy E, the energy of the signal f(2t) is equal to		
	(a) E (b) E/2		
	(c) 2E (d) 4E		
19.	Which of the following is an eigen function of the class of all continuous time		
17.	linear time invariant systems (u(t) denotes unit step function)?		
	$(c) e^{j\omega_0 t}$ $(d) \sin(\omega_0 t)$		
20.	The autocorrelation function of an energy signal has		
20.			
	1 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2		
21.			
21,	The 4-point Discrete Fourier Transform of a discrete time sequence {1, 0, 2,		
	3} is		
	(a) $[0, -2 + 2j, -2-2j]$ (b) $[2, 2+2j, 2-2j]$		
	(c) [6, 1-3j, 2, 1+3j] (d) $[6, -1+3j, 0, -1-3j]$		
22			
22.	The first six points of the 8-point DFT of a real valued sequence are $5, 1-j3$,		
	0, 3-j4,0 and $3+j4$. The last two points of the DFT are respectively		
	(a) $0, 1-j3$ (b) $0, 1+j3$		
	(c) 1 + j3, 5 $(d) 1 - j3, 5$		
23,	The transfer function of a linear system is the		
	(a) ratio of the output, $v_0(t)$, and input, $v_i(t)$		
	(b) ratio of the derivatives of the output and the input		
	(c) ratio of the Laplace transform of the output and that of the input with all		
	initial conditions zeros.		
	(d) none of these		

	(a) which has zeros in the right-half s-plane		
	(b) which has zeros only in the left-half s-plane		
	(c) which has poles in the right-hapf s-plane		
	(d) which has poles in the left-half s-plane		
25.	The impulse response h(t) of a linear time invariant continous time system is		
	described by $h(t) = \exp(\alpha t)u(t) + \exp(\beta t)u(t)$ and α and β are real constants.		
	This system is stable for		
	(a) α is positive and β is positive (b) α is negative and β is negative		
	(c) α is positive and β is negative (d) α is negative and β is positive		
26.	n-type silicon is obtained by doping silicon with		
	(a) Germanium (b) Aluminium		
	(c) Boron (d) Phosphorus		
27.	The band gap of silicon at room temperature is		
	(b) 0.7 aV		
	(a) 1.3 eV (b) 0.7 eV (c) 1.1 eV (d) 1.4 eV		
	(d) 1.1 eV		
28.	Under low level injection assumption, the injected minority carrier current		
	through for an extrinsic semiconductor is essentially the		
	(a) Diffusion current (b) Drift current		
	(c) Recombination current (d) Induced current		
29.	Drift current in semiconductors depends upon		
	(a) only the electric field		
	(b) only the carrier concentration current		
	(c) Both the electric field and carrier concentration		
30.	(d) Neither the electric field nor the carrier concentration	-	
50.	Under high electric fields, in a semiconductor with increasing electric field, (a) The mobility of charge carriers decreases		
	(b) The mobility of charge carriers decreases		
	(c) The velocity of charge carriers saturates		
	(d) The velocity of charge carriers increases		
31.	The diffusion potential across a P-N junction		
	(a) decreases with increasing doping concentration		
	(b) increases with decreasing band gap		
	(c) does not depend on doping concentrations		
	(d) increases with increase in doping concentration		
32.	Schottky diode turns off		
	(a) faster w.r.t PN diode (b) slower w.r.t PN diode		
	(c) same speed (d) none of the above		
33.	Which of the following exhibits devices exhibits negative resistance		
	characteristics		
	(a) Photo diode (b) Zener diode		
	(c) Tunnel diode (d) MOSFET		
34.	A tunnel diode is best suited for		
	(a) Very low frequencies (b) Very low frequencies		
	(c) Microwave frequencies (d) none of the above		
35.	Which of the following devices has the highest input resistance		
55.	(a) diode (b) JFET		

36.	A zener diode works on the principle of	
	(a) tunnelling of charge carriers across the	unction
	(b) thermo ionic emission	
	(c) diffusion of charge across the junction	
	(d) accumulation of charge carriers across t	he junction
37.	For small signal ac operation, a practical fo	
	modelled as	
	(a) a resistance and a capacitance	
	(b) an ideal diode and resistance in parallel	
	(c) a resistance and a ideal diode in series	
	(d) a resistance	
38.	The static characteristic of an adequately fo	arward hiased n-n junction is a
20.	straight line, if the plot is	i wara olasea p il juliettoli is a
	(a) logI vs logV	(b) logI vs V
	(c) I vs logV	(d) I vs V
39	A zener diode, when used in voltage stabili	
37.	(a) Reverse bias region below the breakdow	
	(b) Reverse breakdown region	vii region
	1	
	(c) Forward bias region (d) Forward bias constant current mode	
40	3.6	
40.	The Ebers-Moll model is applicable to	
	(a) Bipolar junction transistors	
	(b) NMOS transistors	
	(c) Unipolar junction transistors	
	(d) Junction field effect transistors	
41.	A FET operates on	
		nority carriers only
		ne of the above
42.	Thermal runaway is not possible in FET be increases	cause as the temperature of FET
	(a) the transconductance increases (1)	b) the drain current increases
	(c) the mobility of the carriers decreases (c	d) none of the above
43.	Which of the following devices is used at the	
	voltmeter	
	(a) BJT (b) SCR	
	(c) MOSFET (d) UJT	
44.	MOSFET can be used as a	
	(a) Current controlled capacitor	(b) Voltage controlled capacitor
	(c) Current controlled inductor	(d) Voltage controlled inductor
45.	In a MOSFET, the polarity of the inversion	
,	(a) charge on the electrode	(b) minority carries in the drain
	(c) majority carries in the substrate	(d) majority carries in the source
46.	The DC current gain (β) of a BJT is 50. Ass	
τυ.	efficiency is 0.995, the base transport factor	
	(a) 0.980	(b) 0.985
	(a) 0.980 (c) 0.990	(d) 0.985
17		- N. C.
47.	A MOS capacitor made using p-type substra	
	The dominant charge in the channel is due t	•
	(a) Holes	(b) Electrons
	(c) Positively charged ions	(d) negatively charged ions

48.	A DC power supply has a No-load voltage if 30V and a full-load voltage if 25V at a full-load current of 1A. The output resistance and load regulation		
	respectively are		
	(a) 5 Ω and 20% (b) 25 Ω and 20%		
	(c) 5 Ω and 16.7% (d) 25 Ω and 16.7%		
49.	A BJT is said to be operating in the saturation region if		
	(a) Both the Junction are reverse biased		
	(b) Base-Emitter junction is reverse biased and Base-collector junction is		
	forward biased		
	(c) Base-Emitter junction is forward biased and Base-collector junction is		
	reverse biased		
	(d) Both the junctions are forward biased		
50.	In a bipolar transistor at room temperature, if the emitter current is doubled the		
	voltage across its base-emitter junction		
	(a) doubles (b) halves		
	(c) increase by about 20 mV (d) decrease by about 20 mV		
51.	The current gain of a BJT is		
	$(a) g_m r_o (b) g_m / r_o$		
	$(c) g_{m} r_{\pi} \qquad (d) g_{m} / r_{\pi}$		
52.	A cascade Amplifier stage is equivalent to		
	(a) A common emitter stage followed by a common base stage		
	(b) A common base stage followed by an Emitter follower		
	(c) An Emitter follower stage followed by a common base stage		
	(d) A common base stage followed by a common Emitter stage		
53.	The cascade amplifier is a configuration of		
	(a) CC-CB (b) CE-CB		
E 1	(c) CB-CC (d) CE-CC		
54.	If the emitter resistance in a common-emitter voltage amplifier is not		
	bypassed, it will		
	(a) reduce both the voltage gain and the input impendence (b) reduce the voltage gain and increase the input impendence		
	(c) increase the voltage gain and reduce the input impendence		
	(d) increase both the voltage gain and the input impendence		
55.	In a multistage EC-Coupled amplifier the coupling capacitor		
J U 11	(a) limits the low frequency response		
	(b) limits the high frequency response		
	(c) does not effect the frequency response		
	(d) blocks the d.c components without effecting the frequency response		
56.	The current of a bipolar transistor drops at high frequencies because of		
	(a) Transistor capacitances		
	(b) High current effects in the base		
	(c) Parasitic inductive elements		
	(d) The Early effect		
57.	Generally, the gain of a transistor amplifier falls at high frequency due to		
	(a) Internal capacitances of the device		
	(b) Coupling capacitor at the input		
	(c) Skin effect		
	(d) Coupling capacitor at the output		

58.	An n-channel depletion MOSFET has the	e following two points on its I _D - V _{GS}
	curve:	
	(i) $V_{GS} = 0$ at $I_D = 12$ mA and	
	(ii) $V_{GS} = -6$ at $Z_0 = \infty$	4)
	(a) $V_{GS} = -6$ Volts	(b) $V_{GS} = -3 \text{ Volts}$
	(c) $V_{GS} = 0$ Volts	(d) 3 Volts
59.	A change in the value of the Emitter resis	
	(a) affects the difference mode gain A _d	(b) affects the common mode
	gain A _c	
	(c) affects both A _d and A _c	(d) does not affect either A _d or A _c
60.	In a differential amplifier CMRR can be	improved by using an increased
	(a) Emitter resistance	(b) Collector resistance
	(c) Power supply voltage	(d) Source resistance
61.	If the differential voltage gain and the con	mmon mode voltage gain of a
	differential amplifier are 48 dB and 2 dB	
	rejection ratio is	
	(a) 23 dB	(b) 25 dB
	(c) 46 dB	(c) 50 dB
62.	An ideal op-amp is a ideal	(7)
	(a) voltage controlled current source	
	(b) voltage controlled voltage source	
	(c) current controlled current source	
	(d) current controlled voltage source	
63.	In case of class A amplifiers, the ratio(eff	ficiency of transformer counled
05.	amplifier)/(efficiency of a transformer less	
	(a) 2.9 (b) 2	ampiritor) is
	(c) 1.0 (d) 0.5	
64.	The range of signed representation number	are that can be represented by 6 hit
04.	1's complement number is	ers that can be represented by 6-bit
	(a) -31 to +31	(h) (2 to 1 (2
	The Action of the Control of the Con	(b) -63 to +63
(5	(c) -64 to +64	(d) -32 to +31
65.	2's compliment representation of a 16-bit	
	magnitude bits) is FFFF. Its magnitude in	
	Hode to	0)1
		1) 65,535
66.	An equivalent 2's complement representa	ation of the 2's complement number
	1101 is	
	(a) 110100	(b) 001101
	c) 110111	(d) 111101
67.	4-bit 2's complement representation of a	decimal number is 1000. The number
	is	
	(a) +8 (b) 0	
	(c) -7 (d) -8	
68.	Decimal 43 in Hexadecimal and BCD nu	mber system is respectively.
	(a) B2, 0100 0011 (b) 2B, 0	0100 0011
	(c) 2B, 0011 0100 (d) B2, 0	0100 0100

69.	X = 01110 and $y = 11001$ are two 5-bit complement format. The sum of x and	*
	format using 6bits is	y represented in two s complement
	(a) 100111 (b) 001	000
	(c) 000111 (d) 101	
70.	11001, 1001 and 111001 correspond to	the 2's complement representation of
	which one of the following sets of num	lber?
	(a) 25, 9 and 57 respectively	
	(b) -6, -6 and -6 respectively	†
	(c) -7, -7 and -7 respectively	
	(d) -25, -9 and -57 respectively	
71.	For a n-variable Boolean function ma	aximum number of prime implicants is
	(a) $2(n-1)$ (b) $n/2$	
	(c) 2^n (d) $2^{(n-1)}$	
72.	The Boolean function $Y = AB + CD$ is	
	NAND gates. The minimum number of	
	(a) 2	(b) 3
73.	(c) 4 Indicate which of the following logic g	(d) 5
15	combinational logic functions	ates can be used to realize an possible
	(a) OR gates only	(b) NAND gates only
	(c) EX-OR gates only	(d) None of the above
74.	A bulb in a staircase has two switches,	
	and the other one at the first floor. The	bulb can be turned ON also be turned
	OFF by any one of the switches irrespe	ctive of the other switch. The logic of
	switching of the bulb resembles	4.)
	(a) an AND gate	(b) an OR gate
75.	(c) an XOR gate	(d) a NAND gate
13.	What are the minimum number of 2-to-2-input AND gate and a 2-input EX-OF	
	(a) 1 and 2	(b) 1 and 3
	(c) 1 and 1	(c) 2 and 2
76.	A 0 to 6 counter consists of 3 flip-flops	
	gate(s). The combination circuit consist	
	(a) one AND gate	(b) one OR gate
	(c) one AND gate and one OR gate	(d) two AND gates
77.	The number of comparators in a 4-bit fl	
	(a) 4	(b) 5
78.	(c) 15 A PLL can be used to demodulate	(d) 16
70.	(a) Pam signals	(b) PCM signals
	(c) FM signals	(d) DC+SB-SC signals
79.	The image channel selectivity of super	
	(a) IF amplifiers only	apenas upon
	(b) RF and IF amplifiers only	
	(c) Pre selector, RF and IF amplifiers	
	(d) Pre selector and RF amplifiers only	

80.	An AM signal and a narrow band FM signal with identical carriers, modulating signals and modulation indices of 0.1 are added together. The		
	resultant signal can be closely approximated by		
	(a) Broadband Fm (b) SSB with carrier		
	(c) DSB-SC (c) SSB without carrier		
81.	In a radar receiver the antenna is connected to the receiver through a		
	waveguide. Placing the preamplifier on the antenna side of the waveguide		
	rather than on the receiver side leads to:		
	(a) A reduction in the overall noise figure		
	(b) A reduction in interference		
	(c) An improvement in selectivity characteristics		
	(d) An improvement in directional characteristics		
82.	The maximum power efficiency of an AM modulator is		
	(a) 25 % (b) 50 %		
	(b) 75 % (d) 100 %		
83.	An FM signal with a modulation index 9 is applied to a frequency tripler. The		
	modulation index in the output signal will be		
	(a) 0 (b) 3		
	(b) 9 (d) 27		
84.	Two sinusoidal signals of same amplitude and frequencies 10 kHz and 10.1		
	kHz are added together. The combined signal is given to an ideal frequency		
	detector. The output of the detector is		
	(a) 0.1 kHz sinusoid (b) 20.1 kHz sinusoid		
	(c) a linear function of time (d) a constant		
85.	If the number of bits per sample in a PCM system is increased from n to $n + 1$,		
05.	the improvement in signal to quantization noise will be		
	(a) 3 dB (b) 6 dB		
	(c) 2n dB (d) n dB		
86.	In a PCM system with uniform quantization, increasing the number of bits	-	
00.	from 8 to 9 will reduce the quantization noise power by a factor of		
	(a) 9 (b) 8		
	(c) 4 (d) 2		
87.	In a binary data transmission DPSK is preferred over PSK because		
. , .	(a) a coherent carrier is required to be generated at the receiver		
	(b) for a given energy per bit, the probability of error is less		
	(c) the 180° phase shifts of the carrier are unimportant		
	(d) more protection is provide against impulse noise		
	Colores and a series are a series and a seri		
88.	Coherent demodulation of FSK signal can be effected using		
	(a) correlation receiver (b) band pass filters and envelope detectors		
	(c) matched filters (d) discrimination detection		
39.	The number of hardware interrupts (which require an external signal to	-	
· / •	interrupt) present in an 8085 microprocessor are		
	(a) 2 (b) 4		
	(a) 2 (c) 5 (d) 8		
90.			
, O.	In the 8085 microprocessor, the RST6 instruction transfers the program		
	execution to the following location		
	(a) 30 H (b) 24 H		
	(c) 48 H (d) 60H		

	are A7 (in hex) and 0, respectively. If the instruction RLC is executed, then the contents of the accumulator (in hex) and the carry flag, respectively, will be	
	(a) 4E and 0 (b) 4E and 1	
	(c) 4F and 0 (d) 4F and 1	
92.	An I/O processor control the flow of information between	
	(a) cache memory and I/O devices	
	(b) main memory and I/O devices	
	(c) two I/O devices	
00	(d) cache and main memory	
93.	A microprocessor with a 16-bit address bus is used in a linear memory	
	selection configuration (i.e. address bus lines are directly used as chip selects	
	of memory chips) with 4 memory chips. The maximum addressable memory	
	space is	
	(a) 4 K (b) 16 K	
94.	(c) 64 K (d) 8 K	
94.	In an 8085 microprocessor system, the RST instruction will cause an interrupt	
	(a) only if an interrupt service routine is not being executed (b) only if a bit in the interrupt mask is made 0	
	(c) only if interrupts have been enabled by an EI instruction	
	(d) none of the above	
95.	In an 8085 microprocessor system with memory mapped I/O,	
	(a) I/O devices have 8 bit address	
	(b) I/O devices are accessed using IN and OUT instructions	
	(c) there can be a maximum of 256 input devices and output devices	
	(d) arithmetic and logic operations can be directly performed with the I/O data	
96.	Air friction damping is used in the instrument which is	
	(a) moving iron (b) moving coil	
	(c) induction (d) hot wire	
97.	Which of the following is absolute instrument?	
	(a) power factor meter (b) Ammeter	
	(c) wattmeter (d) tangent galvanometer	
98.	Which of the following types of instrument is an integrating instrument?	
	(a) power factor meter (b) energy meter	
	(c) wattmeter (d) frequency meter	
99.	The controlling torque in a spring controlled meter is proportional to	
	(a) θ (b) θ^2	
400	(c) $1/\theta$ (d) $1/\theta^2$	
100.	The internal resistance of the multi-ammeter must be very low for	
	(a) high sensitivity	
	(b) high accuracy	
	(c) maximum voltage drop across the meter	